

# SANYO Semiconductors DATA SHEET

## MCH6732-

NPN Epitaxial Planar Silicon Transistor

— Schottky Barrier Diode

### **DC / DC Converter Applications**

#### **Features**

- Composite type with a NPN transistor and a Schottky barrier diode contained in one package facilitatiing high-density mounting.
- Ultrasmall package permitting applied sets to be small and slim (mounting height 0.85mm).

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit						
[TR]										
Collector-to-Base Voltage	VCBO		20	V						
Collector-to-Emitter Voltage	VCEO		15	V						
Emitter-to-Base Voltage	VEBO		5	V						
Collector Current	IC		1	Α						
Collector Current (Pulse)	ICP		2	Α						
Collector Dissipation	PC	Mounted on a ceramic board (600mm <sup>2</sup> X0.8mm)	0.7	W						
Junction Temperature	Tj		150	°C						
Storage Temperature	Tstg		-55 to +125	°C						
[SBD]										
Repetitive Peak Reverse Voltage	VRRM		15	V						
Non-repetitive Peak Reverse Surge Voltage	VRSM		15	V						
Average Output Current	IO		0.5	Α						
Surge Current	IFSM	50Hz sine wave, 1 cycle	2	Α						
Junction Temperature	Tj		-55 to +125	°C						
Storage Temperature	Tstg		-55 to +125	°C						

Marking : PG

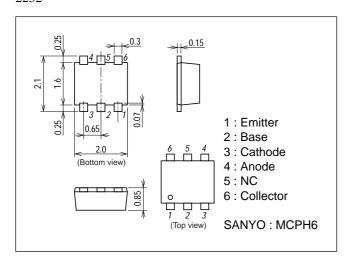
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#### Electrical Characteristics at Ta=25°C

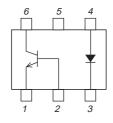
Parameter	Symbol	Conditions	Ratings			Unit			
			min	typ	max	Offic			
[TR]									
Collector Cutoff Current	ICBO	V <sub>CB</sub> =12V, I <sub>E</sub> =0			0.1	μΑ			
Emitter Cutoff Current	IEBO	VEB=4V, IC=0			0.1	μΑ			
DC Current Gain	hFE	VCE=2V, IC=50mA	300		800				
Gain-Bandwidth Product	fT	V <sub>CE</sub> =2V, I <sub>C</sub> =50mA		440		MHz			
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		4		pF			
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =400mA, I <sub>B</sub> =20mA		140	280	mV			
Base-to-Emitter Saturation Voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> =400mA, I <sub>B</sub> =20mA		0.9	1.2	V			
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0	20			V			
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	15			V			
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V			
Turn-ON Time	ton	See specified Test Circuit.		30		ns			
Storage Time	tstg	See specified Test Circuit.		165		ns			
Fall Time	tf	See specified Test Circuit.		25		ns			
[Di]									
Reverse Voltage	VR	I <sub>R</sub> =0.5mA	12			V			
Forward Voltage	VF	IF=0.5A		0.40	0.45	V			
Reverse Current	IR	V <sub>R</sub> =6V			90	μΑ			
Interterminal Capacitance	С	V <sub>R</sub> =10V, f=1MHz		13		pF			
Reverse Recovery Time	t <sub>rr</sub>	IF=IR=100mA, See specified Test Circuit.			10	ns			

#### **Package Dimensions**

unit : mm 2232



#### **Electrical Connection**



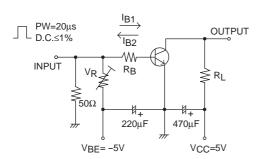
1 : Emitter 2 : Base 3 : Cathode 4 : Anode 5 : NC

6: Collector

Top view

#### **Switching Time Test Circuit**

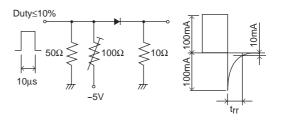
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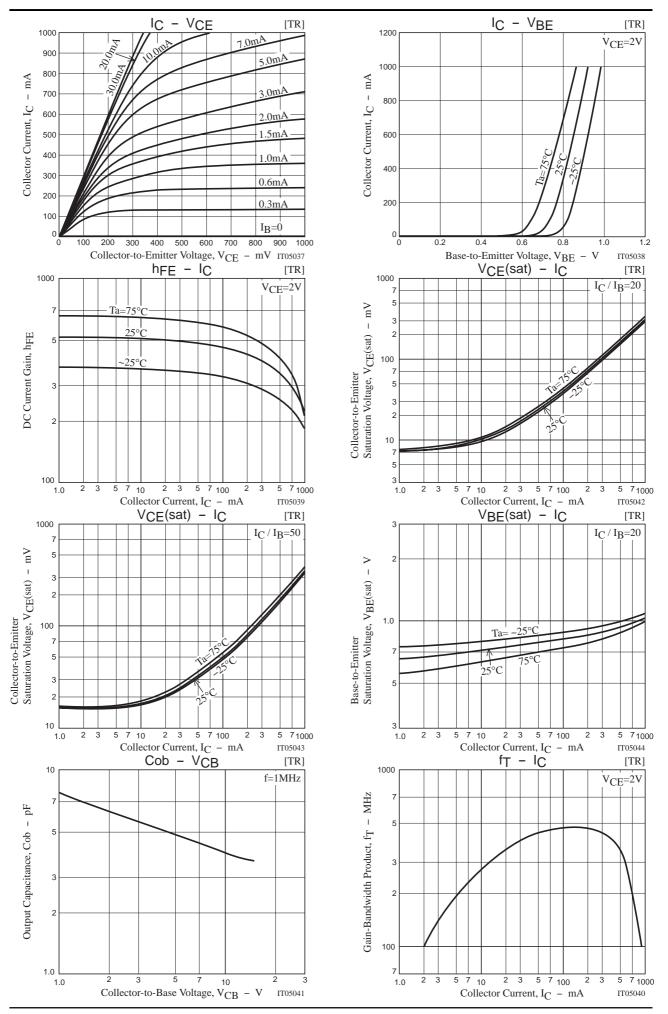


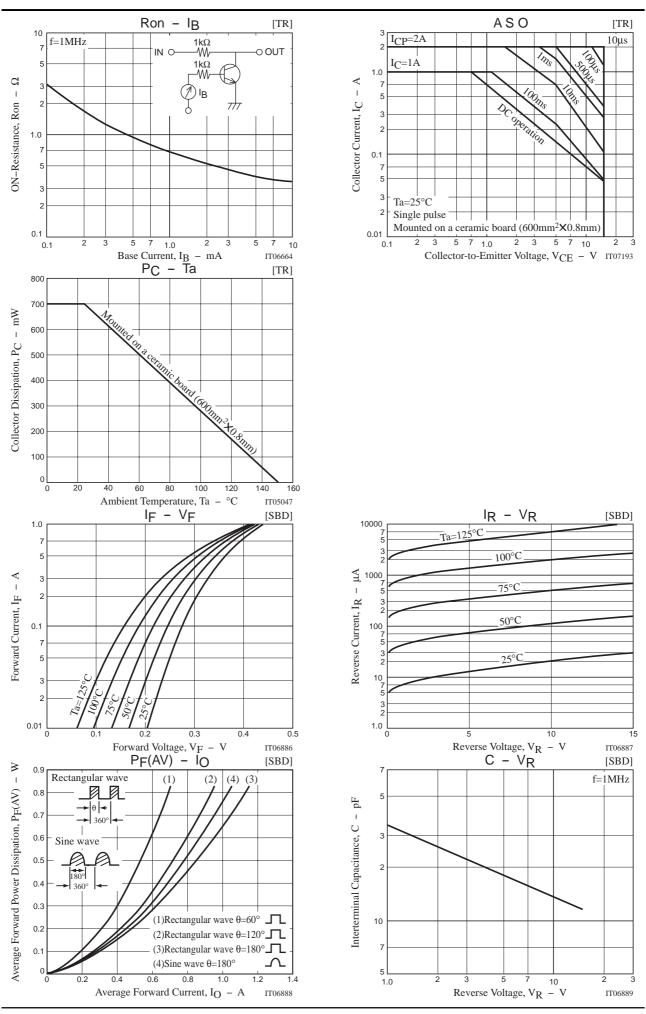
 $I_{C}=20I_{B1}=-20I_{B2}=400mA$ 

#### trr Specified Circuit

[Di]







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